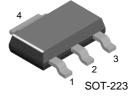


# April 2006

## FZT3019 NPN General Purpose Amplifier

#### **Features**

- This device is designed for general purpose medium power amplifiers and switches requiring collector currents to 500 mA and collector voltages up to 80 V.
- · Sourced from process 12.



1. Base 2. Collector 3. Emitter

### Absolute Maximum Ratings \* $T_a = 25$ °C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	80	V
$V_{CBO}$	Collector-Base Voltage	140	V
V <sub>EBO</sub>	Emitter-Base Voltage	7.0	V
I <sub>C</sub>	Collector current - Continuous	1.0	Α
T <sub>J</sub> , T <sub>stg</sub>	Junction and Storage Temperature	-55 ~ +150	°C

<sup>\*</sup> These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Charac	teristics				•
V <sub>(BR)CEO</sub>	Collector-Emitter Sustaining Voltage *	$I_C = 30 \text{ mA}, I_B = 0$	80		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_E = 0$	140		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 100 μA, I <sub>C</sub> = 0	7.0		Vn
I <sub>CBO</sub>	Collector Cutoff Current	$V_{CB} = 90 \text{ V}, I_{E} = 0$ $V_{CB} = 90 \text{ V}, I_{E} = 0, T_{a} = 150^{\circ}\text{C}$		10 10	nA μA
I <sub>EBO</sub>	Emitter-Cutoff Current	V <sub>EB</sub> = 5 V,		10	nΑ
On Charac	teristics			•	
h <sub>FE</sub>	DC Current Gain	$\begin{split} I_{C} &= 0.1 \text{ mA, V}_{CE} = 10 \text{ V} \\ I_{C} &= 10 \text{ mA, V}_{CE} = 10 \text{ V} \\ I_{C} &= 150 \text{ mA, V}_{CE} = 10 \text{ V} \\ I_{C} &= 500 \text{ mA, V}_{CE} = 10 \text{ V} \\ I_{C} &= 1.0 \text{ A, V}_{CE} = 10 \text{ V} \end{split}$	50 90 100 50 15	300	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.2 0.5	V V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 150 mA, I <sub>B</sub> = 15 mA		1.1	V
	al Characteristics	-		•	
f <sub>T</sub>	Current Gain - Bandwidth Product	I <sub>C</sub> = 50 mA, V <sub>CE</sub> = 10 V, f = 20 MHz	100		MHz
C <sub>cob</sub>	Collector-Base Capacitance	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1.0 MHz		12	pF
C <sub>ibo</sub>	Input Capacitance	V <sub>BE</sub> = 0.5 V, I <sub>E</sub> = 0, f = 1.0 MHz		60	pF
h <sub>fe</sub>	Small Signal current Gain	I <sub>C</sub> = 50 mA, V <sub>CE</sub> = 10 V, f = 20 MHz	80	400	
rb'Cc	Collector Base Time Constant	I <sub>C</sub> = 10 mA, V <sub>CB</sub> = 10 V, f = 4.0 MHz		400	pS
NF	Noise Figure	$I_C = 100 \text{ mA}, V_{CE} = 10 \text{ V},$ $R_S = 1.0 \text{k}\Omega, f = 1.0 \text{KHz}$		4.0	dB

<sup>\*</sup> Pulse Test: Pulse Width  $\leq 300~\mu s,$  Duty Cycle  $\leq 2.0\%$ 

<sup>1.</sup> These ratings are based on a maximum junction temperature of 150 degrees  ${\bf C}.$ 

<sup>2.</sup> These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

## Thermal Characteristics $T_a$ =25°C unless otherwise noted

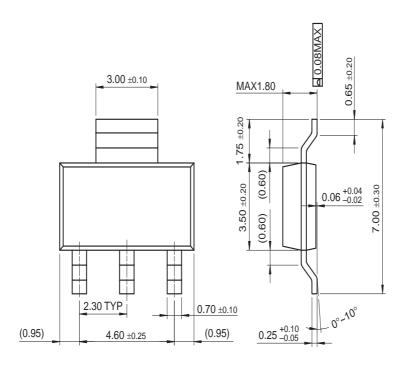
Symbol	Parameter	Max.	Units
$P_{D}$	Total Device Dissipation	1.0	W
	Derate above 25°C	8.0	mW/°C
R <sub>θJA</sub> *	Thermal Resistance, Junction to Ambient	125	°C/W

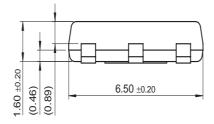
NOTES :

<sup>\*</sup> Device mounted on FR-4 PCB 36mm × 18mm ×1.5mm, Mounting Pad for the collector lead is 600mm<sup>2</sup>

## **Package Dimensions**

## **SOT-223**





**Dimensions in Millimeters** 

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